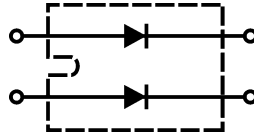


Fast Recovery Epitaxial Diode (FRED)

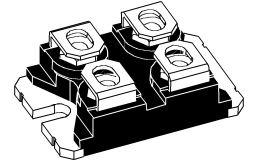
DSEI 2x 121

**$I_{FAVM} = 2x 123 A$
 $V_{RRM} = 200 V$
 $t_{rr} = 35 ns$**

V_{RSM} V	V_{RRM} V	Type
200	200	DSEI 2x 121-02A



miniBLOC, SOT-227 B
E72873

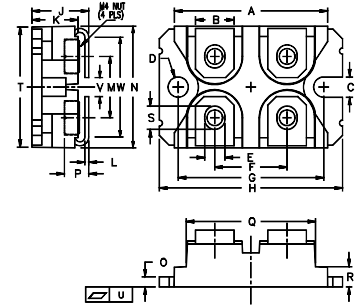


Symbol	Test Conditions	Maximum Ratings (per diode)	
I_{FRMS}	$T_{VJ} = T_{VJM}$	150	A
I_{FAVM} ①	$T_C = 70^\circ C$; rectangular, $d = 0.5$	123	A
I_{FRM}	$t_p < 10 \mu s$; rep. rating, pulse width limited by T_{VJM}	600	A
I_{FSM}	$T_{VJ} = 45^\circ C$; $t = 10 ms$ (50 Hz), sine	1200	A
	$t = 8.3 ms$ (60 Hz), sine	1300	A
	$T_{VJ} = 150^\circ C$; $t = 10 ms$ (50 Hz), sine	1080	A
	$t = 8.3 ms$ (60 Hz), sine	1170	A
I^2t	$T_{VJ} = 45^\circ C$; $t = 10 ms$ (50 Hz), sine	7200	A ² s
	$t = 8.3 ms$ (60 Hz), sine	7100	A ² s
	$T_{VJ} = 150^\circ C$; $t = 10 ms$ (50 Hz), sine	5800	A ² s
	$t = 8.3 ms$ (60 Hz), sine	5700	A ² s
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+150	°C
P_{tot}	$T_C = 25^\circ C$	250	W
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 mA$	2500	V~
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
Weight		30	g

Features

- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 2500 V~
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
I_R	$T_{VJ} = 25^\circ C$		1m
	$T_{VJ} = 25^\circ C$	$I_R = 0.8 \cdot V_{RRM}$	0.5
	$T_{VJ} = 125^\circ C$	$I_R = 0.8 \cdot V_{RRM}$	20
V_F	$I_F = 120 A$; $T_{VJ} = 150^\circ C$ $T_{VJ} = 25^\circ C$	0.89	0.95
V_{TO}	For power-loss calculations only		0.7
r_T	$T_{VJ} = T_{VJM}$		2.1
R_{thJC}			0.5
R_{thCK}		0.1	
t_{rr}	$I_F = 1 A$; $-di/dt = 400 A/\mu s$; $V_R = 30 V$; $T_{VJ} = 25^\circ C$	5	50
I_{RM}	$V_R = 100 V$; $I_F = 100 A$; $-di/dt = 200 A/\mu s$ $L \leq 0.05 \mu H$; $T_{VJ} = 100^\circ C$	2	15

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $d = 0.5$
Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

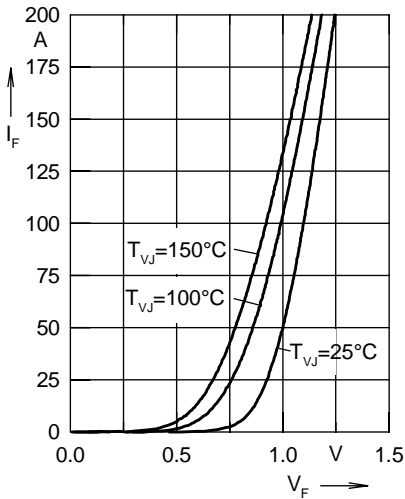


Fig. 1 Forward current I_F versus V_F

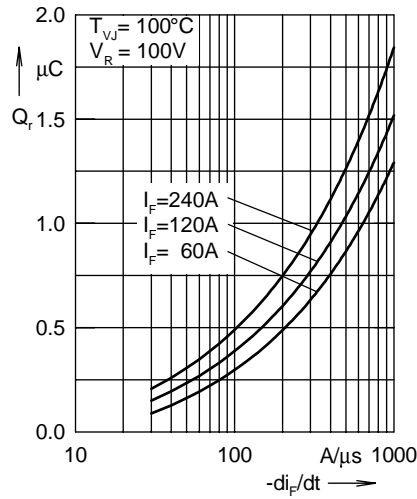


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

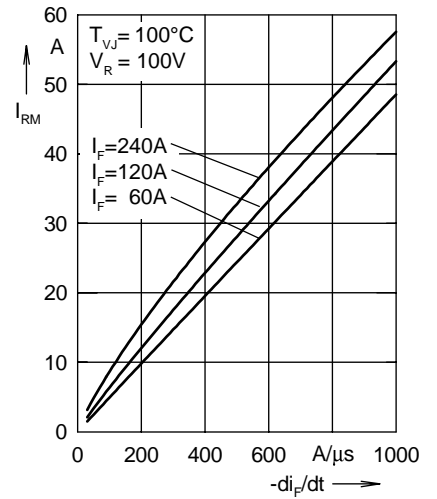


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

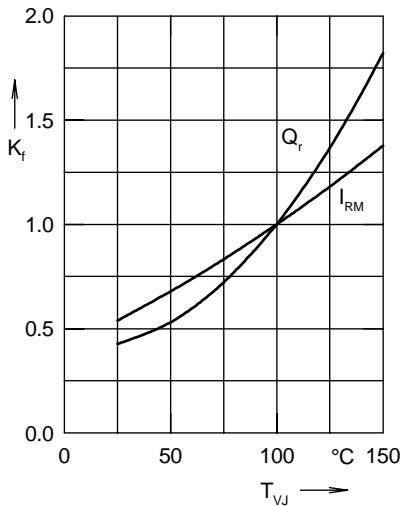


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

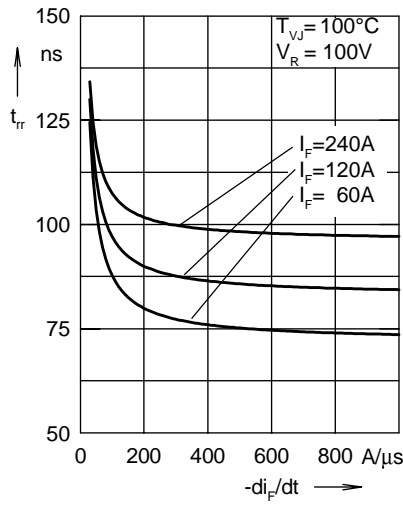


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

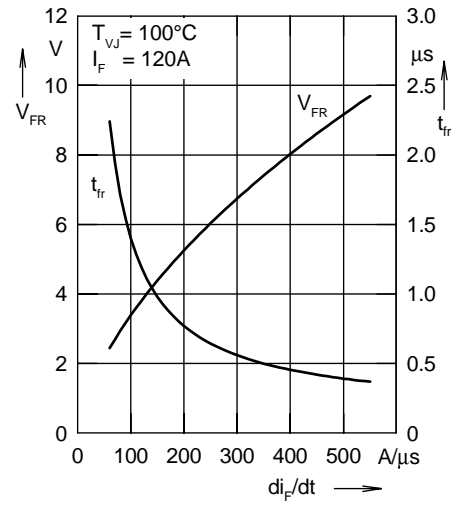


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

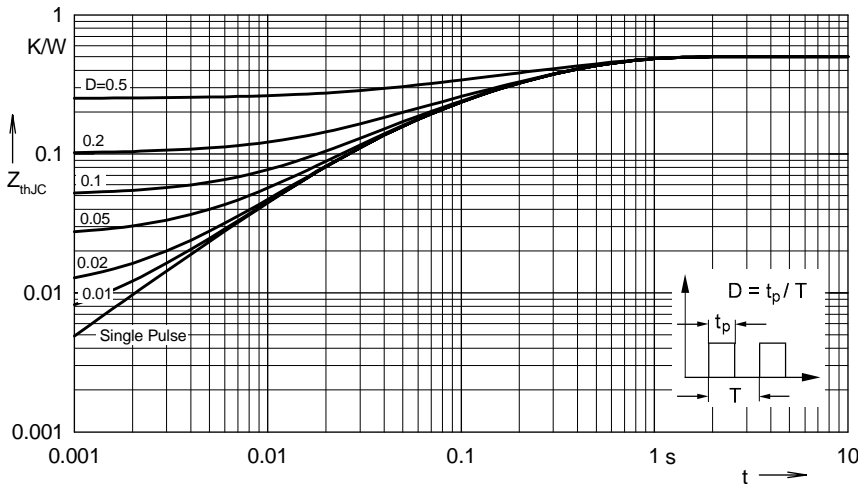


Fig. 7 Transient thermal impedance junction to case at various duty cycles

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0725	0.028
2	0.1423	0.092
3	0.2852	0.35